O Z N A M

Vo výberovom konaní vyhlásenom dekanom Fakulty elektrotechniky a informatiky STU v Bratislave, ktoré sa konalo dňa 6.6.2024 na obsadenie :

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Údaje o publikačnej činnosti:

K2.1	NEČAS, V., SEKÁČOVÁ, K., LY ANH, T., PERĎOCHOVÁ, A. Preliminary Results of Gamma Irradiated Semi-Insulating GaAs Detectors. In Proceedings of the 5th international workshop APCOM 1999 (Applied Physics of Condensed Matters), Bratislava, Slovakia: SUT, 1999, pp.134-137.
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K2.5	PERĎOCHOVÁ, A., LY ANH, T., NEČAS, V., DUBECKÝ, F. Optimalization of Semi-Insulating GaAs Detektor of Ionizing Radiation for Modern Digital Radiography. In Proceedings of the 7th International Workshop APCOM 2001 (Applied

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K2.7	LY ANH, T., PERĎOCHOVÁ, A., NEČAS, V., DUBECKÝ, F.: SI GaAs Detector Performances after High Doses of Gamma Radiation, Proceedings of the 8th International Workshop APCOM 2002 (Applied Physics of Condensed Materials), eds. J. Mudroň, J. Müllerová et al., Liptovský Mikuláš (Slovakia), Military Academy, 2002, pp. 99-104.
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K2.10	PERĎOCHOVÁ, A. et al. The Influence of SI GaAs Detector Topology on Detection Properties. In Proceedings of the 9th International Workshop APCOM 2003 (Applied Physics of Condensed Matter). Žilina, Slovakia: University of Žilina, 2003, pp. 96-100. ISBN 80-8070-088-5.
K2.11	LY ANH, T., PERĎOCHOVÁ, A. et al. Radiation Hardness of SI GaAs Detectors to Gamma Photons. In Proceedings of the 9th International Workshop APCOM 2003 (Applied Physics of Condensed Matter). Žilina, Slovakia: University of Žilina, 2003, pp. 101-106. ISBN 80-8070-088-5.
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K2.13	PERĎOCHOVÁ, A., DUBECKÝ, F., LY ANH, T., NEČAS, V., BOHÁČEK, P., SEKÁČOVÁ, M. The Role of Semi-Insulating GaAs Detector Topology in Detection Performances. In Proceedings of the XIIth International Conference on Semiconducting and Insulating Materials SIMC-XII-2002. Smolenice Castle, Slovakia, 2002, pp. 265-268. 0-7803-7418-5/02/$17.00©2002 IEEE
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K2.15	DUBECKÝ, F., ZAŤKO, B., NEČAS, V., ŠČEPKO, P., GAJTANSKÁ, M., SEKÁČOVÁ, M., PERĎOCHOVÁ, A., SEKERKA, V., HURAN, J., BOHÁČEK, P., AND HUDEC, M. Development and Performance of Imaging Radiation Detector based on Semi-insulating GaAs: Application in □-ray Computer Tomograph for

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	International Conference on Advanced Semiconductor Devices and Microsystems (ASDAM 2004). Smolenice Castle, Slovakia, 2004, pp. 243 – 246.
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K2.27	DUBECKÝ, F., MAKOVNÍK, M., PIVARČI, M., BOHÁČEK, P., SEKÁČOVÁ, M, ZAŤKO, B., LINHART, V., ŠAGÁTOVÁ-PERĎOCHOVÁ, A. and POSPÍŠIL, S.: Performance study of semi-insulating GaAs radiation detectors II: Role of electrode metallization. In Proceedings of the 12th International Workshop APCOM 2006 (Applied Physics of Condensed Matter). Malá Lučivná, Slovakia: Slovak University of Technology in Bratislava, 2006, pp. 331-334. ISBN 80-227-2424-6.
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K1.12	DUBECKÝ, F., BOHÁČEK, P., SEKÁČOVÁ, M., ZAŤKO, B., LALINSKÝ, T., LINHART, V., ŠAGÁTOVÁ-PERĎOCHOVÁ, A. MUDROŇ, J. and POSPÍŠIL, S.: Role of electrode metallization in performance of semi-insulating GaAs radiation detectors. In Nuclear Instruments and Methods in Physics Research A 576 (2007), pp. 87-89.
K2.29	LADZIANSKÝ, M., ŠAGÁTOVÁ-PERĎOCHOVÁ, A., NEČAS, V.: Semi-insulating GaAs thermal neutron detectors and their electrical properties. In Proceedings of the 13th International Conference on APCOM 2007 (Applied Physics of Condensed Matter). Bystrá, Slovakia: University of Žilina in Žilina, 2007, pp. 133-136. ISBN 978-80-8070-709-5.

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Celkovo: K1+K2 =164, K1 = 55. 2020-2024: K1+K2 =41, K1=19

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Počet doktorandov, ktorým je alebo bol školiteľom s určením, koľkí z nich štúdium ku dňu vyhotovenia životopisu riadne skončili: 6/1

Názov študijného odboru, v ktorom bude uchádzač pôsobiť: **Elektrotechnika**

Počet uchádzačov: 1

V Bratislave, 6.6.2024

v. r. prof. Ing. Vladimír Kutiš, PhD.
d e k a n